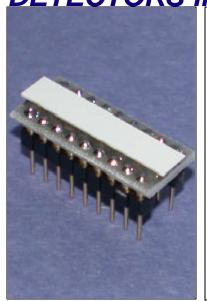
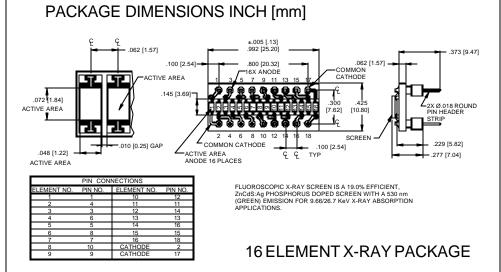
**PHOTONIC** X-RAY, Silicon Photodiode Array, Photoconductive **DETECTORS INC.** (with scintillation screen) Type PDB-C216-S





ACTIVE AREA = 2.31mm<sup>2</sup>

#### **FEATURES**

- .062 inch centers
- Stackable
- Scintillation screen
- Low capacitance

### **DESCRIPTION**

The **PDB-C216-S** is a common cathode, monolithic silicon PIN photodiode 16 element array. Designed to be stacked end to end to form a line of pixels. Supplied with a fluoroscopic X-Ray scintillation screen.

### **APPLICATIONS**

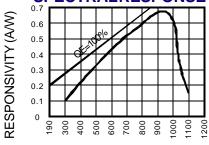
- Luggage X-ray
- X-Ray scanner
- X-Ray inspection

# ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
$V_{\mathtt{BR}}$	Reverse Voltage		50	V
T <sub>STG</sub>	Storage Temperature	-40	+100	⊙C
T <sub>o</sub>	Operating Temperature Range	-20	+75	⊙C
T <sub>s</sub>	Soldering Temperature*		+265	∘C
IL	Light Current		500	mA

<sup>\*1/16</sup> inch from case for 3 secs max

## **SPECTRALRESPONSE**



WAVELENGTH(nm)

### ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted, without scintillator)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
l <sub>sc</sub>	Short Circuit Current	H = 100 fc, 2850 K	18	28		μΑ
I <sub>D</sub>	Dark Current	$H = 0, V_R = 5 V$		5	50	nA
R <sub>SH</sub>	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$	100	200		MΩ
TCR <sub>SH</sub>	RSH Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-8		%/℃
C <sub>J</sub>	Junction Capacitance	$H = 0, V_R = 0 V^{**}$		40	60	pF
λrange	Spectral Application Range	Spot Scan	350		1100	nm
λр	Spectral Response - Peak	Spot Scan		950		nm
V <sub>BR</sub>	Breakdown Voltage	I = 10 μA	15	30		V
NEP	Noise Equivalent Power	V <sub>R</sub> = 10 V @ Peak		2x10 <sup>-14</sup>		W/ √ Hz
tr	Response Time	$RL = 50 \Omega V_R = 10 V$		15		nS